

# Silizium-Pin-Fotodiode mit Tageslichtsperrfilter

Silicon Pin Photodiode with Daylight Filter

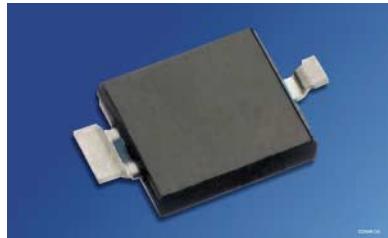
Lead (Pb) Free Product - RoHS Compliant

**BP 104 FAS**

**BP 104 FASR**



BP 104 FAS



BP 104 FASR

## Wesentliche Merkmale

- Speziell geeignet für Anwendungen im Bereich von 730 nm... 1100nm
- Kurze Schaltzeit (typ. 20 ns)
- SMT-fähig

## Anwendungen

- IR-Fernsteuerung von Fernseh- und Rundfunkgeräten, Videorecordern, Lichtdimmern, Gerätefernsteuerungen
- Lichtschranken

## Features

- Especially suitable for applications from 730 nm... 1100nm
- Short switching time (typ. 20 ns)
- Suitable for SMT

## Applications

- IR remote control of hi-fi and TV sets, video tape recorders, dimmers, remote controls of various equipment
- Photointerrupters

Typ Type	Bestellnummer Ordering Code	Fotostrom, $E_e=1 \text{ mW/cm}^2$ , $V_R = 5 \text{ V}$ , $\lambda = 880 \text{ nm}$ Photocurrent $I_p (\mu\text{A})$
BP 104 FAS	Q65110A2672	34 ( $\geq 25$ )
BP 104 FASR	Q65110A4263	34 ( $\geq 25$ )

**Grenzwerte****Maximum Ratings**

<b>Bezeichnung Parameter</b>	<b>Symbol Symbol</b>	<b>Wert Value</b>	<b>Einheit Unit</b>
Betriebs- und Lagertemperatur Operating and storage temperature range	$T_{\text{op}}; T_{\text{stg}}$	- 40 ... + 100	°C
Sperrspannung Reverse voltage	$V_R$	20	V
Verlustleistung, $T_A = 25$ °C Total power dissipation	$P_{\text{tot}}$	150	mW

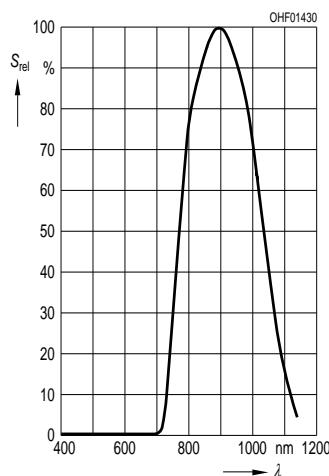
**Kennwerte ( $T_A = 25$  °C,  $\lambda = 880$  nm)****Characteristics**

<b>Bezeichnung Parameter</b>	<b>Symbol Symbol</b>	<b>Wert Value</b>	<b>Einheit Unit</b>
Fotostrom Photocurrent $V_R = 5$ V, $E_e=1$ mW/cm <sup>2</sup>	$I_P$	34 ( $\geq 25$ )	µA
Wellenlänge der max. Fotoempfindlichkeit Wavelength of max. sensitivity	$\lambda_{S \text{ max}}$	880	nm
Spektraler Bereich der Fotoempfindlichkeit $S = 10\%$ von $S_{\text{max}}$ Spectral range of sensitivity $S = 10\%$ of $S_{\text{max}}$	$\lambda$	730 ... 1100	nm
Bestrahlungsempfindliche Fläche Radiant sensitive area	$A$	4.84	mm <sup>2</sup>
Halbwinkel Half angle	$\phi$	$\pm 60$	Grad deg.
Dunkelstrom, $V_R = 10$ V Dark current	$I_R$	2 ( $\leq 30$ )	nA
Spektrale Fotoempfindlichkeit Spectral sensitivity	$S_\lambda$	0.65	A/W
Quantenausbeute Quantum yield	$\eta$	0.90	Electrons Photon
Leerlaufspannung, $E_e = 0.5$ mW/cm <sup>2</sup> Open-circuit voltage	$V_O$	330 ( $\geq 250$ )	mV
Kurzschlussstrom, $E_e = 0.5$ mW/cm <sup>2</sup> Short-circuit current	$I_{\text{sc}}$	16	µA

**Kennwerte** ( $T_A = 25^\circ\text{C}$ ,  $\lambda = 880 \text{ nm}$ )**Characteristics** (cont'd)

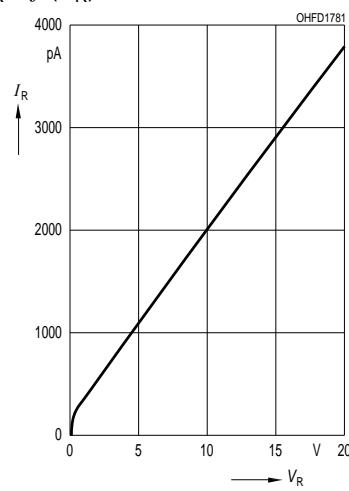
<b>Bezeichnung Parameter</b>	<b>Symbol Symbol</b>	<b>Wert Value</b>	<b>Einheit Unit</b>
Anstiegs- und Abfallzeit des Fotostromes Rise and fall time of the photocurrent $R_L = 50 \Omega$ ; $V_R = 5 \text{ V}$ ; $\lambda = 850 \text{ nm}$ ; $I_p = 800 \mu\text{A}$	$t_r, t_f$	20	ns
Durchlassspannung, $I_F = 100 \text{ mA}$ , $E = 0$ Forward voltage	$V_F$	1.3	V
Kapazität, $V_R = 0 \text{ V}$ , $f = 1 \text{ MHz}$ , $E = 0$ Capacitance	$C_0$	48	pF
Temperaturkoeffizient von $V_O$ Temperature coefficient of $V_O$	$TC_V$	- 2.6	mV/K
Temperaturkoeffizient von $I_{SC}$ Temperature coefficient of $I_{SC}$	$TC_I$	0.18	%/K
Rauschäquivalente Strahlungsleistung Noise equivalent power $V_R = 10 \text{ V}$	$NEP$	$3.6 \times 10^{-14}$	$\frac{\text{W}}{\sqrt{\text{Hz}}}$
Nachweisgrenze, $V_R = 10 \text{ V}$ Detection limit	$D^*$	$6.1 \times 10^{12}$	$\frac{\text{cm} \times \sqrt{\text{Hz}}}{\text{W}}$

**Relative Spectral Sensitivity**  
 $S_{\text{rel}} = f(\lambda)$



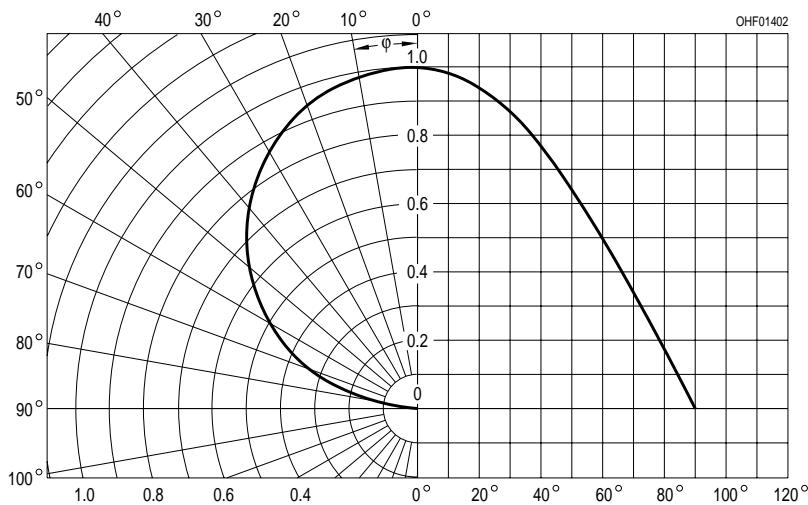
**Dark Current**

$$I_R = f(V_R), E = 0$$

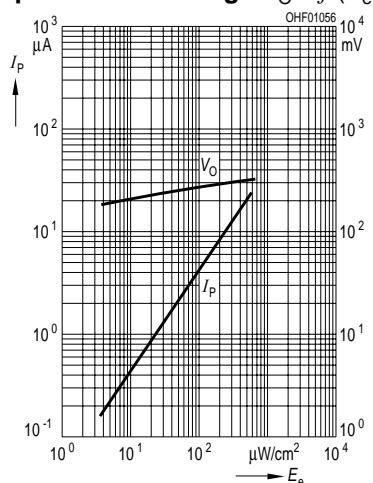


**Directional Characteristics**

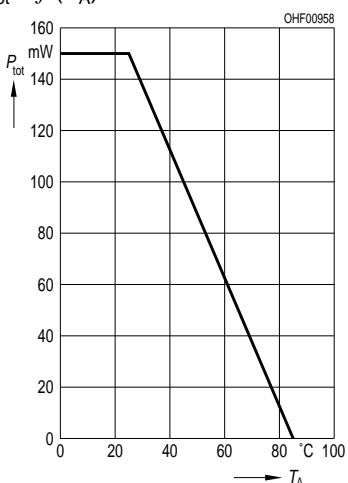
$$S_{\text{rel}} = f(\phi)$$



**Photocurrent  $I_P = f(E_e)$ ,  $V_R = 5 \text{ V}$**   
**Open-Circuit Voltage  $V_O = f(E_e)$**

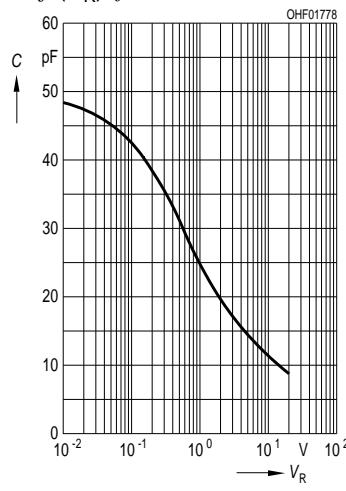


**Total Power Dissipation**  
 $P_{\text{tot}} = f(T_A)$



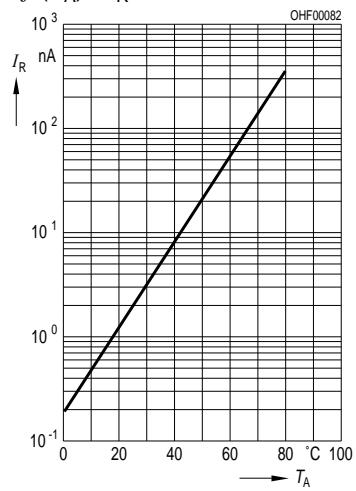
**Capacitance**

$$C = f(V_R), f = 1 \text{ MHz}, E = 0$$

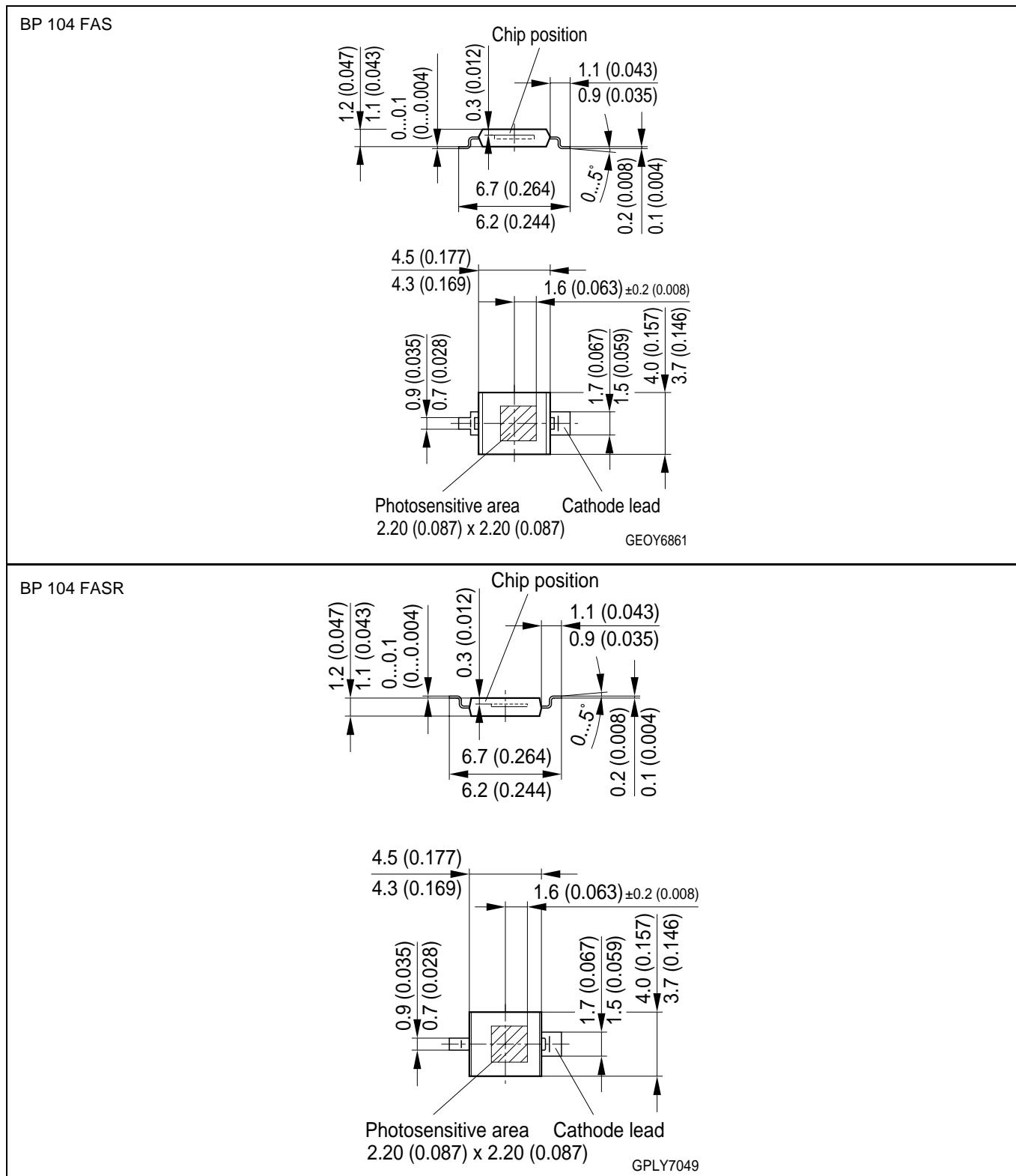


**Dark Current**

$$I_R = f(T_A), V_R = 10 \text{ V}, E = 0$$



# Maßzeichnung Package Outlines



Maße in mm (inch) / Dimensions in mm (inch).

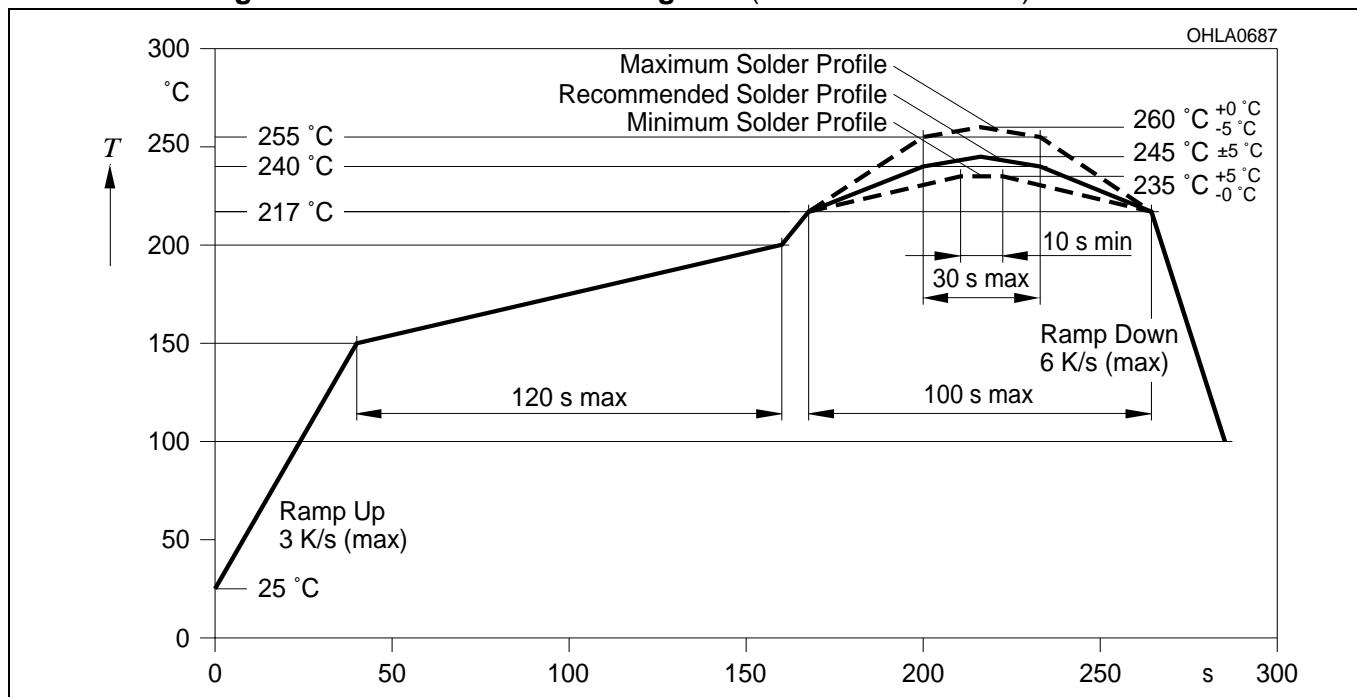
**Lötbedingungen****Soldering Conditions****Reflow Lötprofil für bleifreies Löten****Reflow Soldering Profile for lead free soldering**

Vorbehandlung nach JEDEC Level 4

Preconditioning acc. to JEDEC Level 4

(nach J-STD-020C)

(acc. to J-STD-020C)



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